

Femtosecond time resolved pump-probe spectroscopic ellipsometry – some applications – and some words about long-lasting coherent phonon oscillations in GaP

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thanks to all those who were also strongly involved in development of TSE method and physical understanding of processes: (alphabetically)

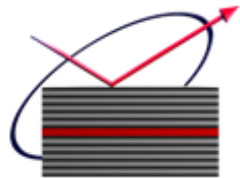
J. Andreasson, C. Emminger, S. Espinoza, D. Franta, O. Herrfurth, K. Hingerl, A. Horn, M. Kloz, J. Leveillee, M. Olbrich, T. Pflug, M. Rebarz, S. Richter, E. Runge, A. Schleife, Y. Slimi, N. Stiehm, C. Sturm, S. Zollner, M. Zahradník

main cooperation:



beamlines

Ellipsometry and
Polariton Physics
Group



The **SPiRiT**
of science

th
TECHNISCHE UNIVERSITÄT
ILMENAU



Why ultrafast dynamics?

(photo-induced) dynamics of the electronic (and phonon) system of materials for understanding and improving of:

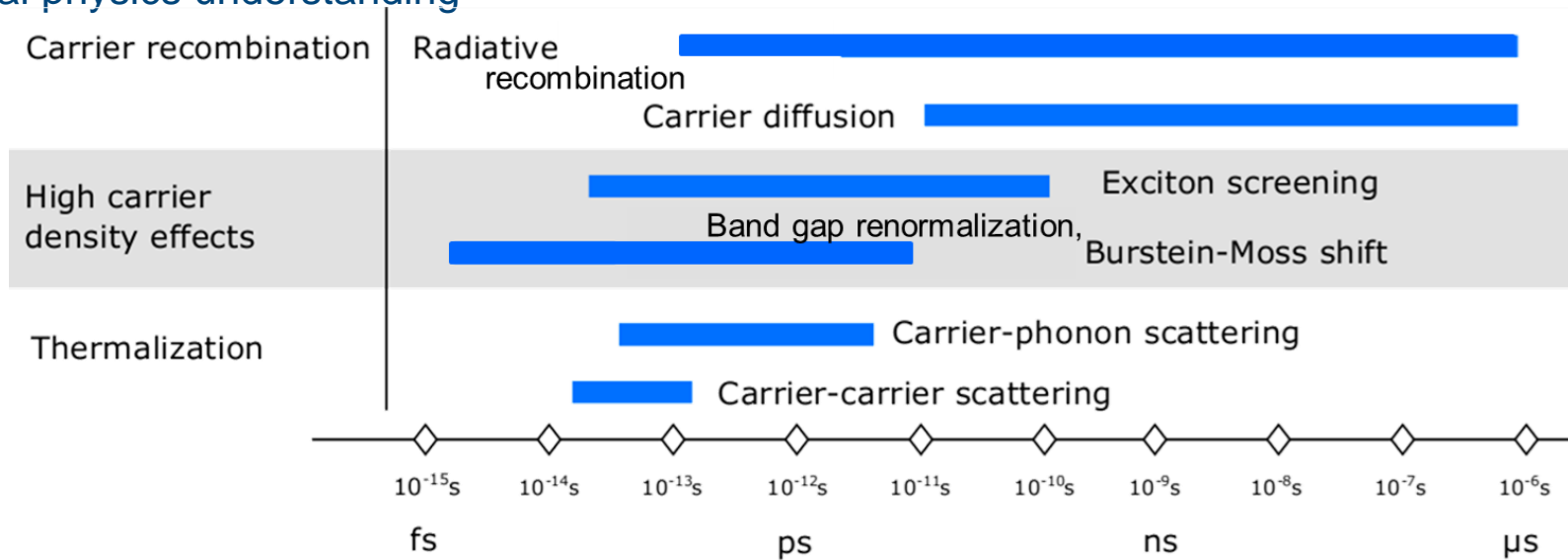
- fundamental understanding
- application in ultra-fast devices
- lightning and optical data transport and processing
- opto-electro-magnetic coupling and switching
- solar energy harvesting

for these applications, knowledge is needed of:

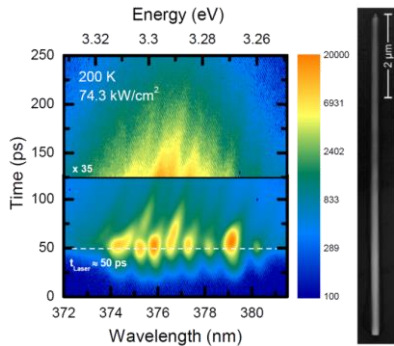
- band structure as well as (joint) density of states and transition matrix elements as function of excited charge carriers
 - excitation, relaxation, scattering, tunnelling and recombination dynamics
 - mechanism which can lead to loss or trapping of excited charge carriers
- time resolved studies – here for example of the dielectric function dynamics after laser excitation

Ultrafast processes

fundamental physics understanding



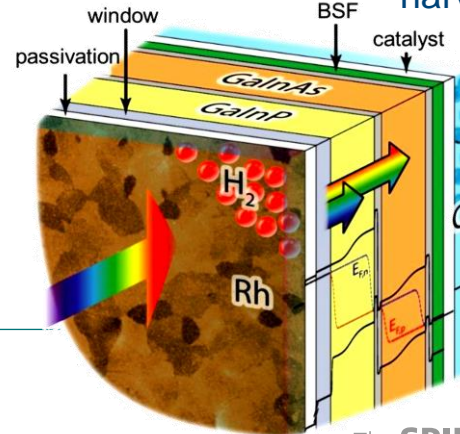
performance of opto-electronic devices, e.g.:



dynamics of lasing modes

M. Wille, RSG et al.: *Nanotechnology* 27 (2016) 225702

light-to-current conversion efficiency in light-harvesting applications



III-V semiconductors
GaP as one of the basic materials

ACS Energy Lett. 3 (2018) 1795

**Today I will tell the tale of charge carriers,
who was sent to a journey through energy and momentum space
after being hit by a strong laser pulse.**

**We have observed their fate by
fs-time resolved spectroscopic pump-probe ellipsometry
and understood it (tried to) by fundamental theory.**

What happens to the charge carriers under absorption of light?

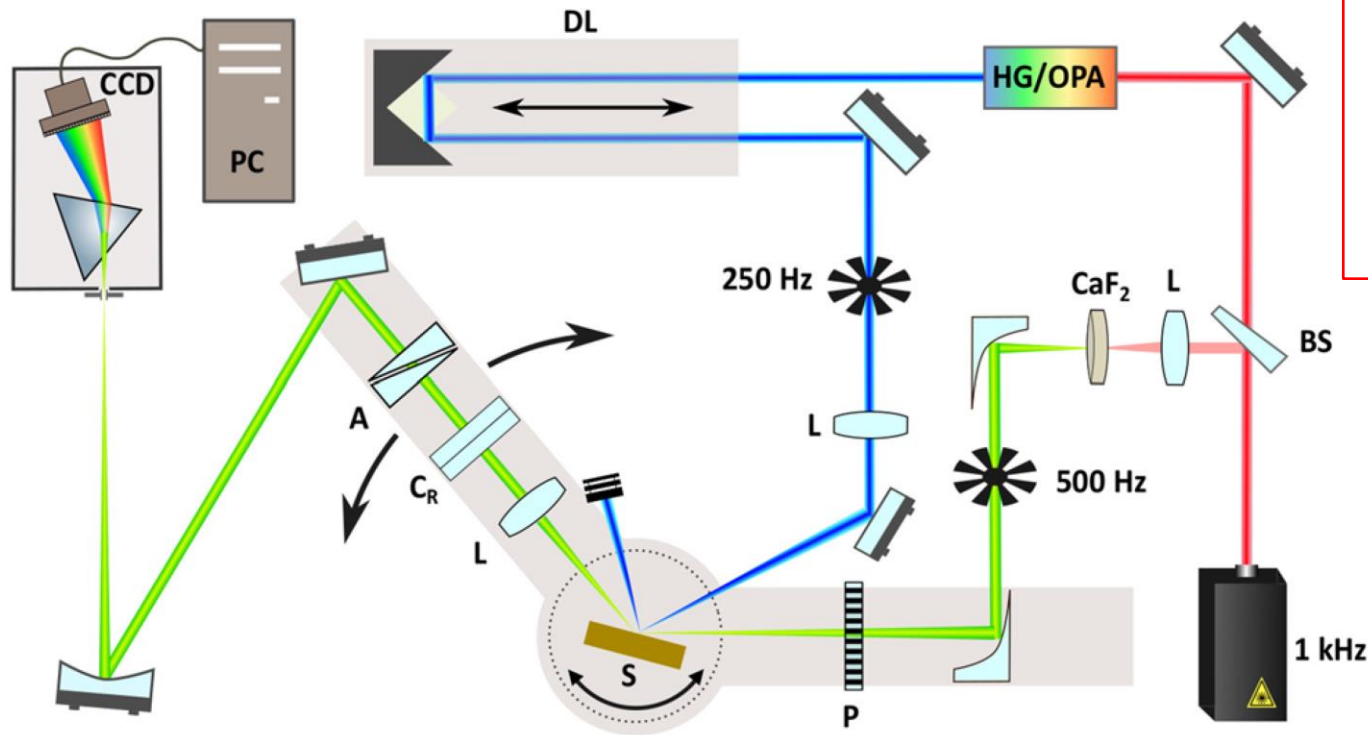
What is their dynamics?

Where do they go to?

Steffen Richter, Mateusz Rebarz, Oliver Herrfurth, Shirly Espinoza, Rüdiger Schmidt-Grund, and Jakob Andreasson, Rev. Sci. Instrum. 92, 033104 (2021)

Broadband femtosecond spectroscopic ellipsometry EP

main work in method development and implementation:
Steffen Richter, Mateusz Rebarz, Oliver Herrfurth but indeed, many others contributed considerably



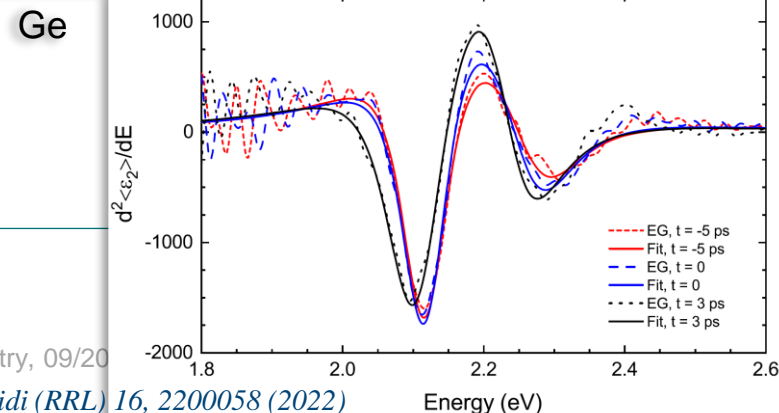
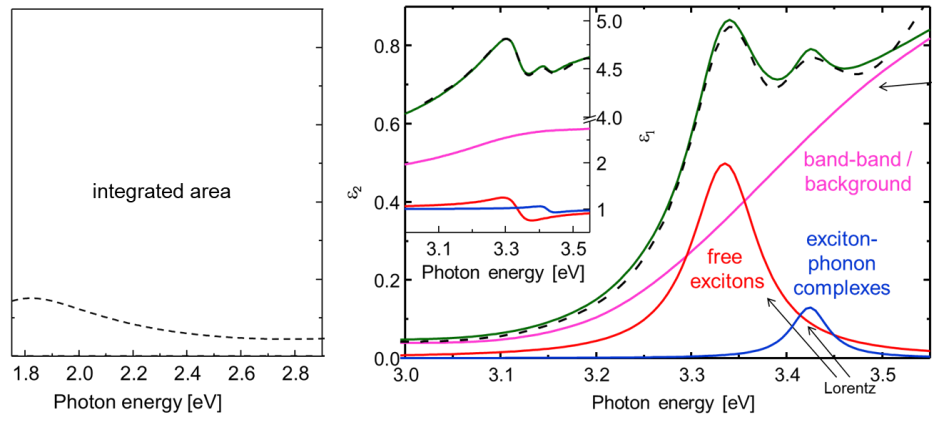
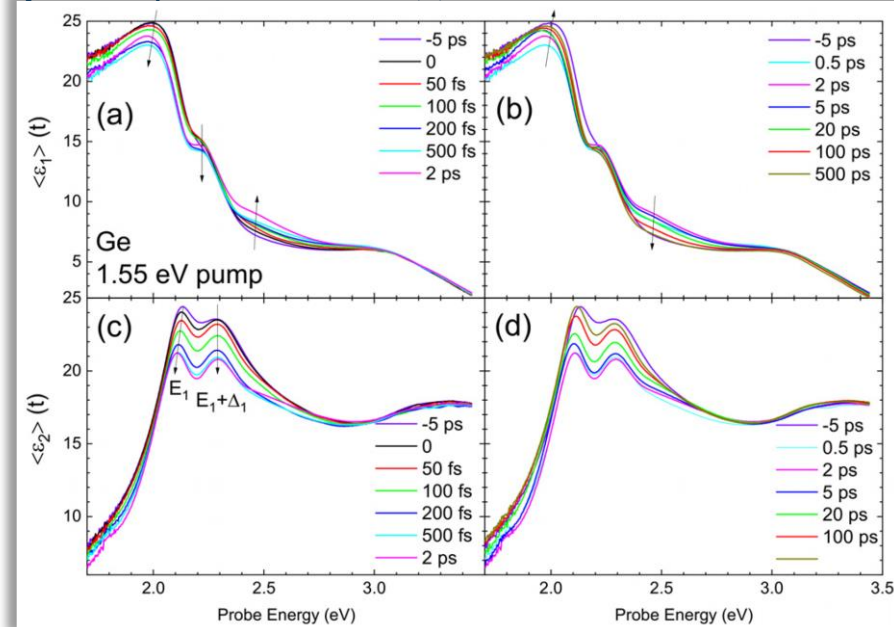
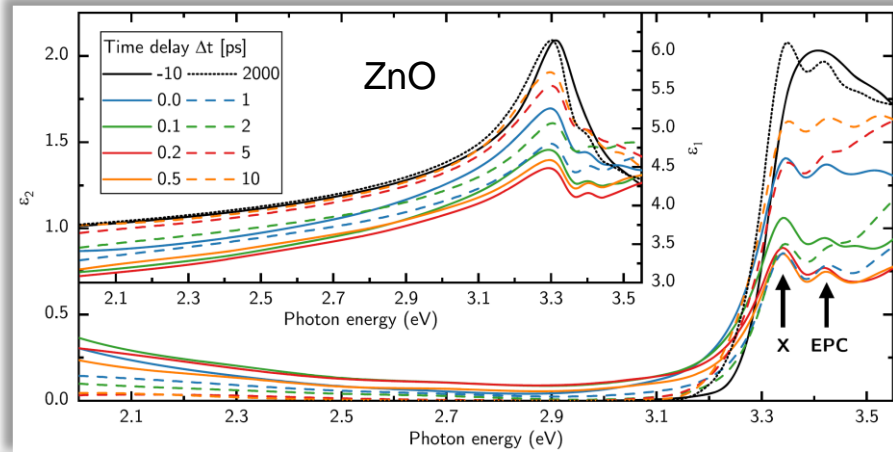
setup build up and located @ ELI beamlines facility in Dolní Břežany (Prague), Czech Republic

Method

Data analysis

we model data for each $\Delta t = \tau$ to obtain the complex DF $\varepsilon(\tau)$

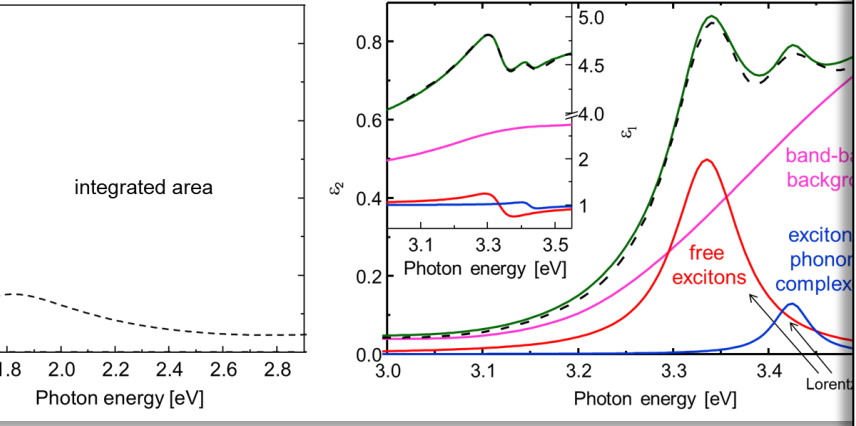
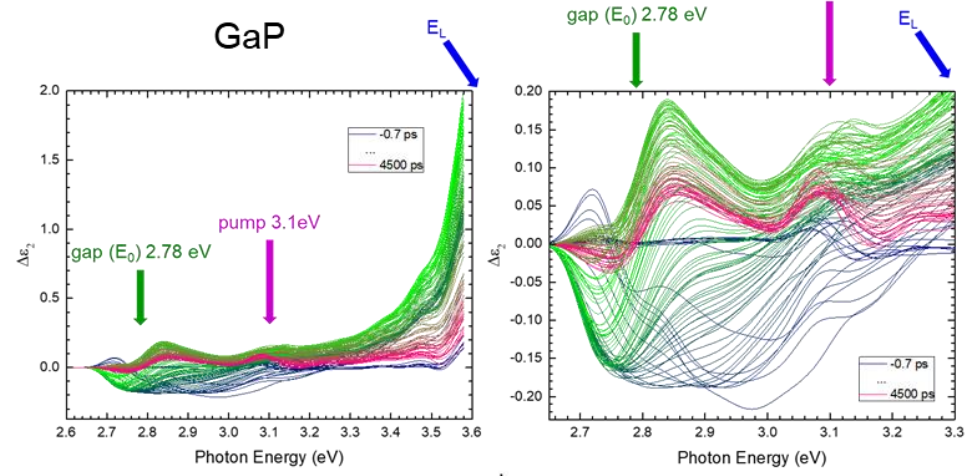
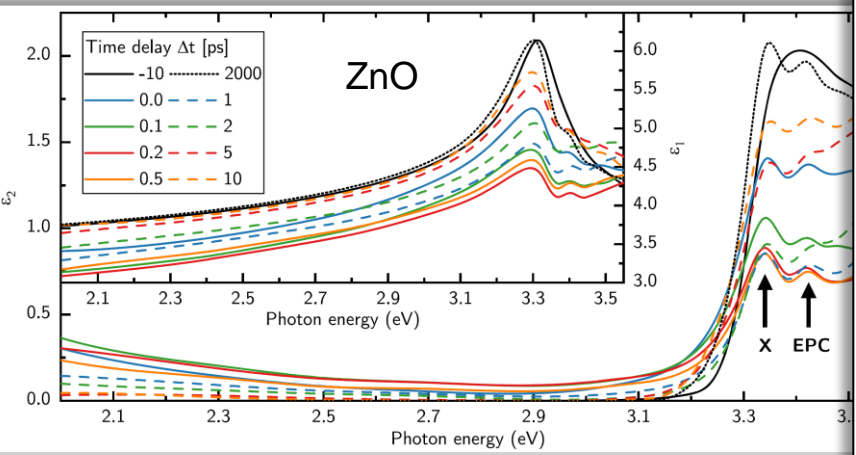
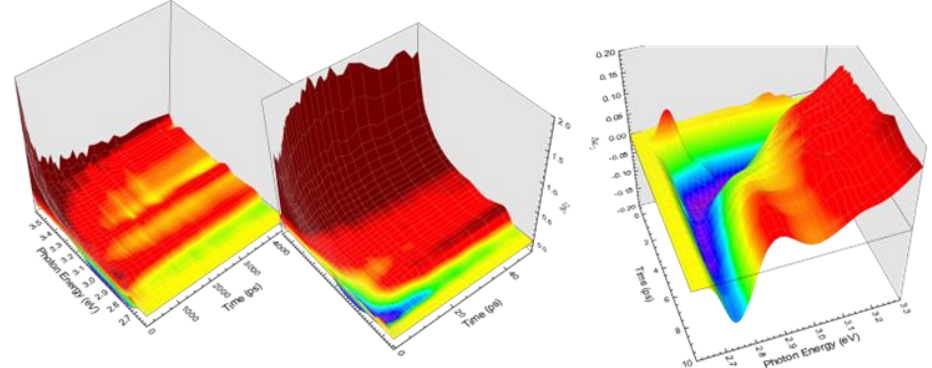
we model either $\varepsilon(\tau)$ or $\Delta\varepsilon(\tau) = \varepsilon(\tau) - \varepsilon(\tau = 0)$ or analyse the pseudo-DF $\langle \varepsilon(\tau) \rangle$



Method

Data analysis

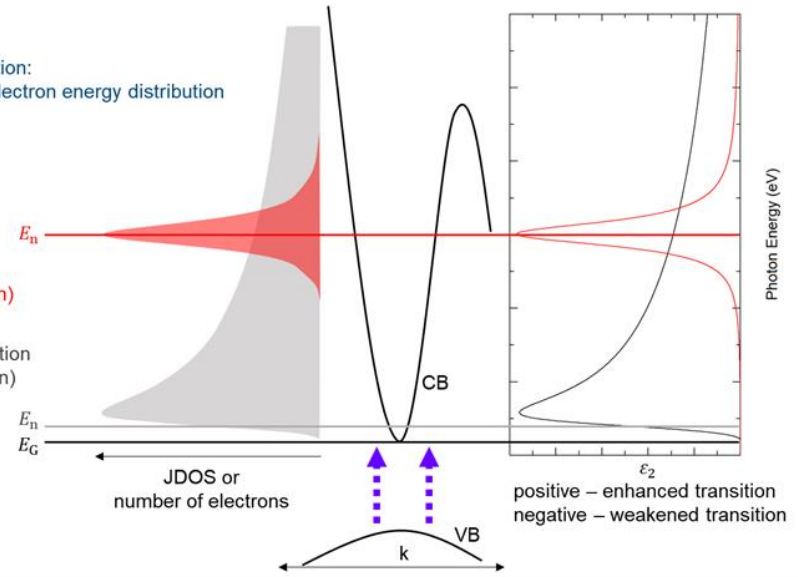
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Tauc-Lorentz function:
 mimics JDOS or electron energy distribution

$E_n \gg E_G$:
 sharp distribution
 (e.g. after excitation)

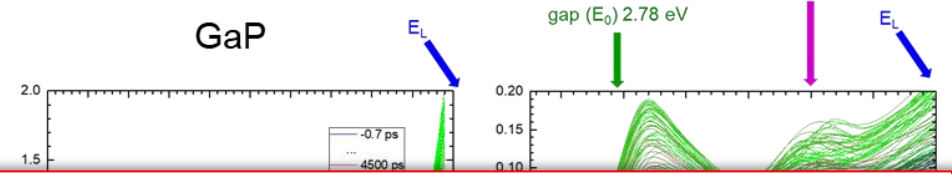
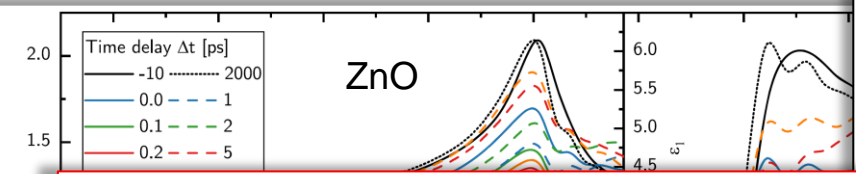
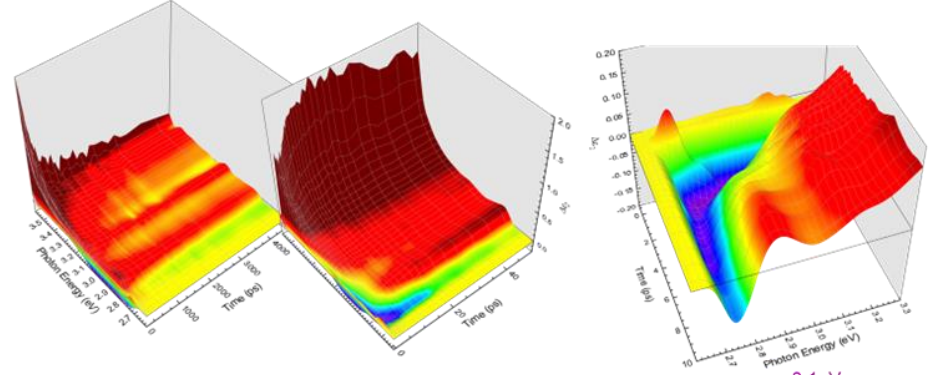
$E_n \approx E_G$:
 broadened distribution
 (e.g. after relaxation)



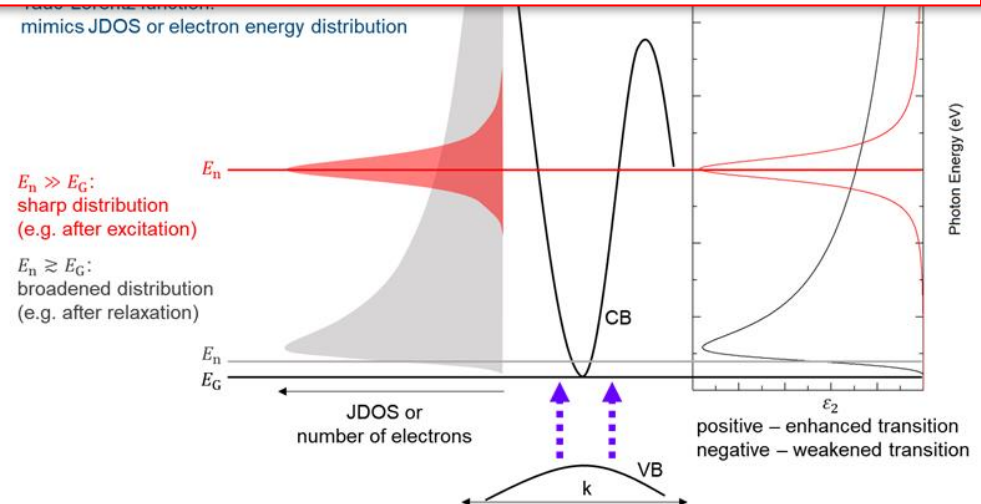
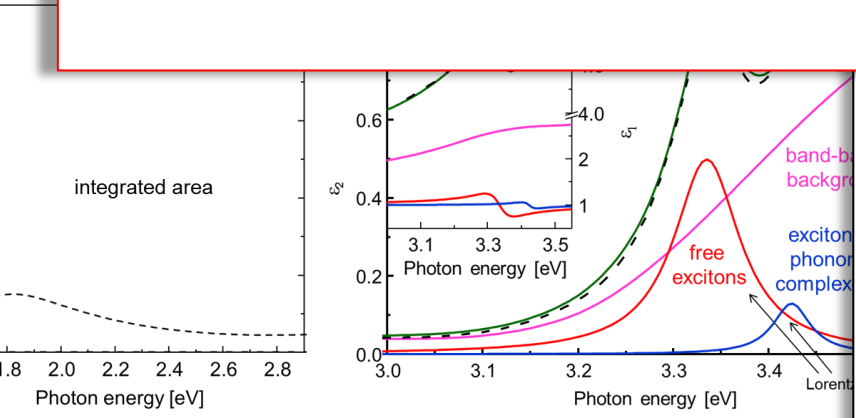
Method

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dielectric function
 energy, amplitude and broadening parameters of electronic transitions
 as well as information on ε_1 background
 as function of time



Method

Compare to fundamental theory

band structure and DF by ground-state plane-wave density functional theory:

transition probability (rate):

$$w_{nm}(\vec{k}, \hbar\omega) = \frac{2\pi}{\hbar} \int_{\vec{k}} |\hat{\mathbf{M}}_{nm}|^2 \delta(E_m(\vec{k}_m) - E_n(\vec{k}_n) \pm \hbar\omega) d\vec{k}$$

with joint density of states

$$\rho_{nm} = \int_{\vec{k}} \delta(E_m(\vec{k}_m) - E_n(\vec{k}_n) \pm \hbar\omega) d\vec{k}$$

and transition dipole matrix element

$$\hat{\mathbf{M}}_{nm} = \langle u_{n,\vec{k}}^{(i)} | \vec{p} | u_{n,\vec{k}}^{(f)} \rangle$$

⇒ dielectric function

(JDOS and Matrix elements between all bands)

transition matrix elements from Kohn-Sham eigenvectors by norm-conserving pseudo-potentials

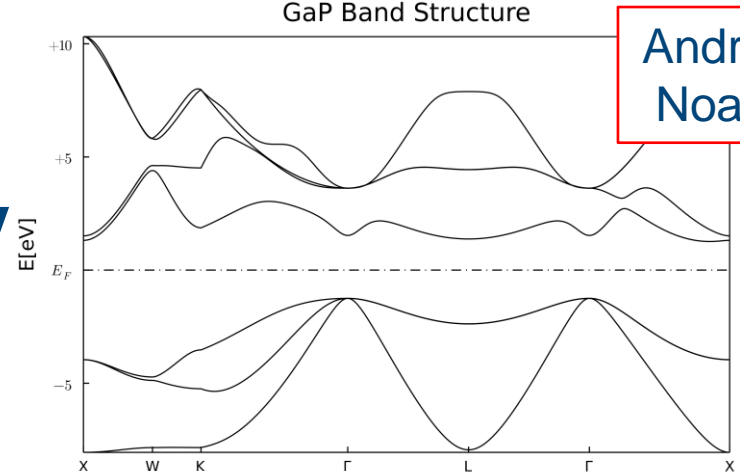
also band symmetries analysed and considered

Charge carrier statistics and Fermi-distributions (carrier temperature, excess-energy)

$$\Delta E_{e/h} = \frac{3}{2} k_B T_{e/h} \quad \Delta E_e = \frac{E_{\text{pump}} - E_{\text{gap}}}{1 + m_e/m_h}$$

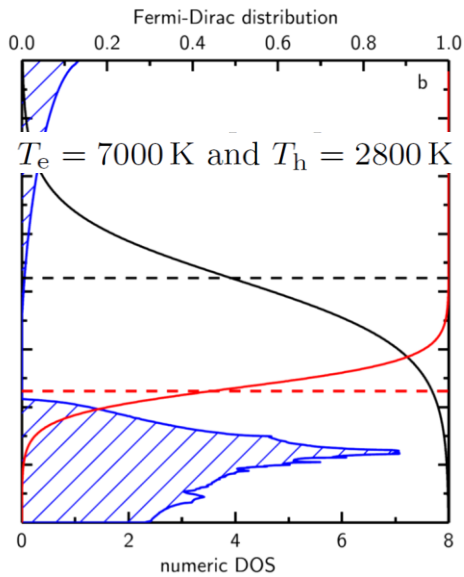
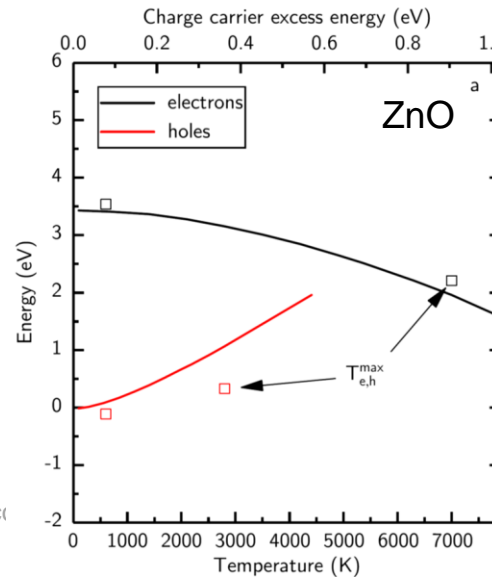
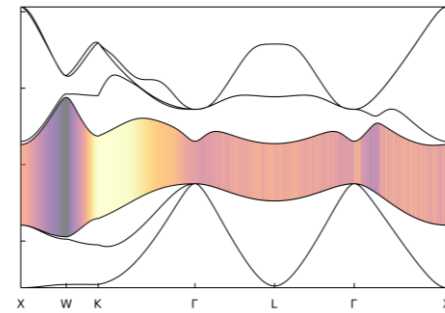
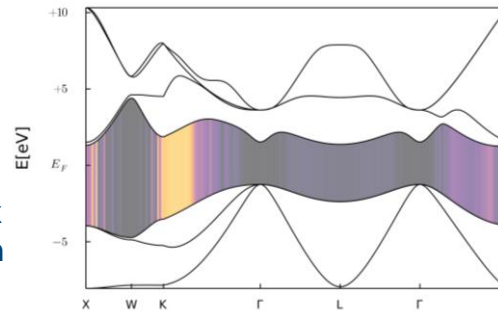
$$\Delta E_h = \frac{E_{\text{pump}} - E_{\text{gap}}}{1 + m_h/m_e}$$

André,
Noah



GaP Band Structure + jDOS

GaP Band Structure + Dipole Matrix Element



The tale of electrons

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after being hit by a strong laser pulse.

We have observed their fate by
fs-time resolved spectroscopic pump-probe ellipsometry
and understood it (tried to) by fundamental theory.

What happens to the charge carriers under absorption of light?

What is their dynamics?

Where do they go to?

let's go through the story – in the world of
optoelectronic (Si, Ge, InP, GaP, ZnO) materials

The tale of electrons

exciting with high-intense laser beam: electrons and holes occupy formerly “empty” conduction (CB) and valence (VB) band states → hot charge carriers with temperatures up to several thousands of Kelvin

- carriers spread within the entire Brillouin zone (BZ) to energetically matching bands
- band gap renormalization (BGR) → redshift of transition energies between VB and CB
- transitions between now occupied states are Pauli-blocked → reduction of absorption at the respective energies
- excess electrons and holes can be excited by the probe light → arising of new intra VB and/or intra CB transitions → increase of absorption at the respective energies
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- collective free charge carrier oscillations (Drude)

in the following time (sub-ps ... ps), excited carriers scatter amongst each other and with the lattice (phonons):

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- phonons oscillate coherently

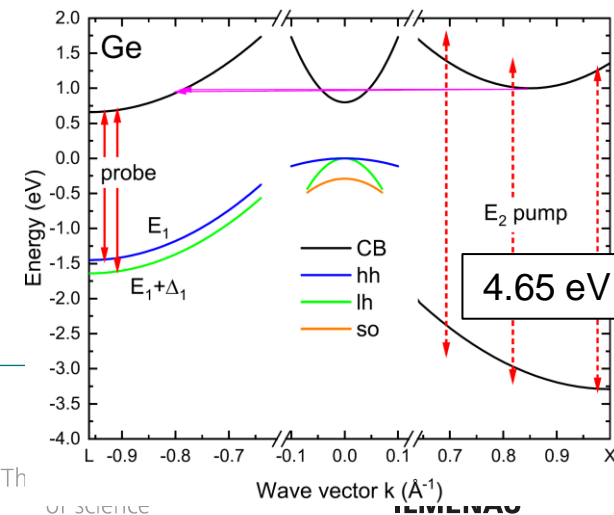
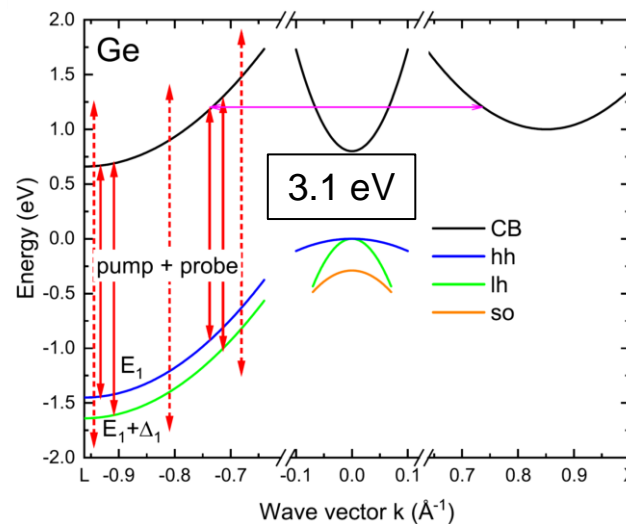
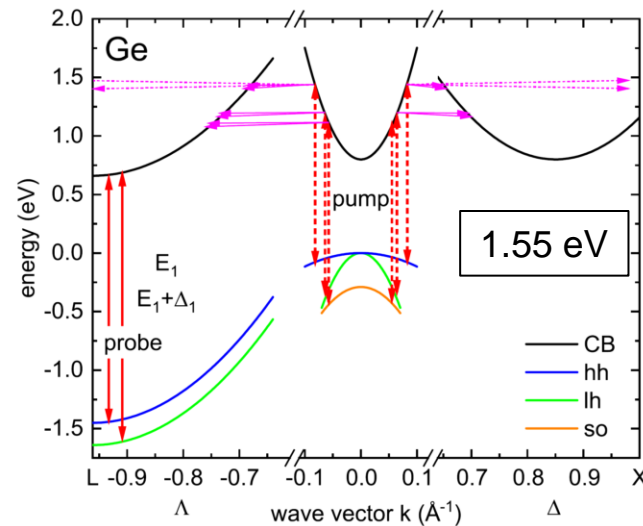
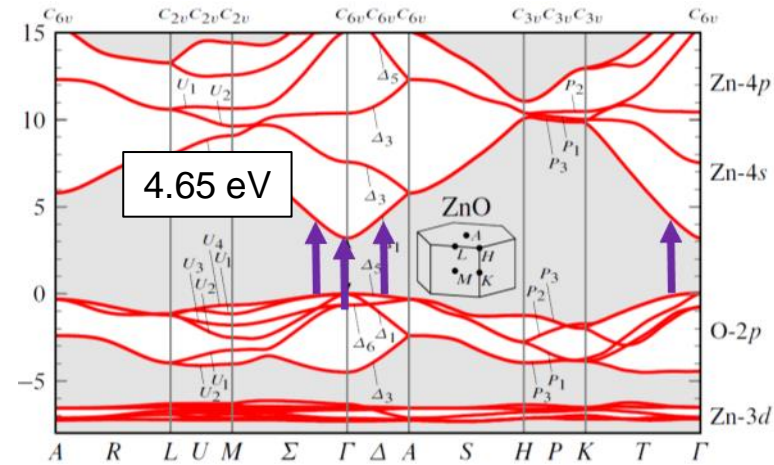
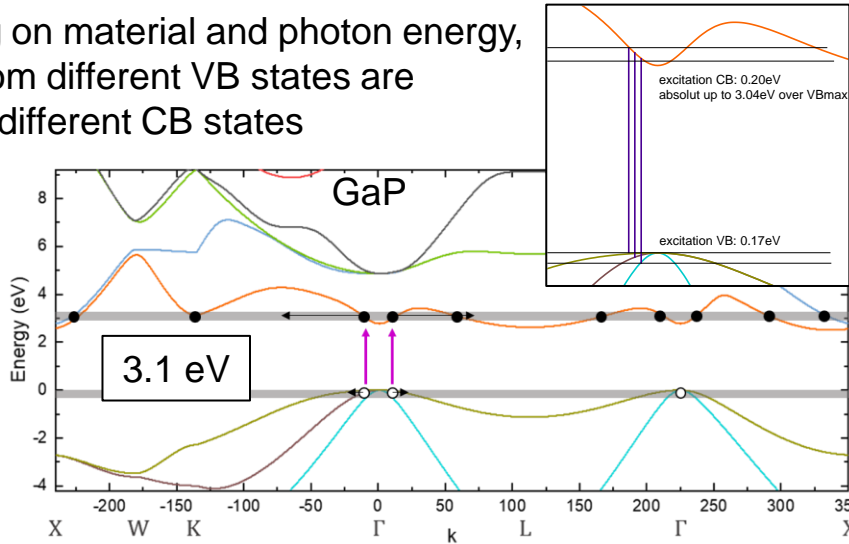
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depending on material and photon energy, carriers from different VB states are excited to different CB states

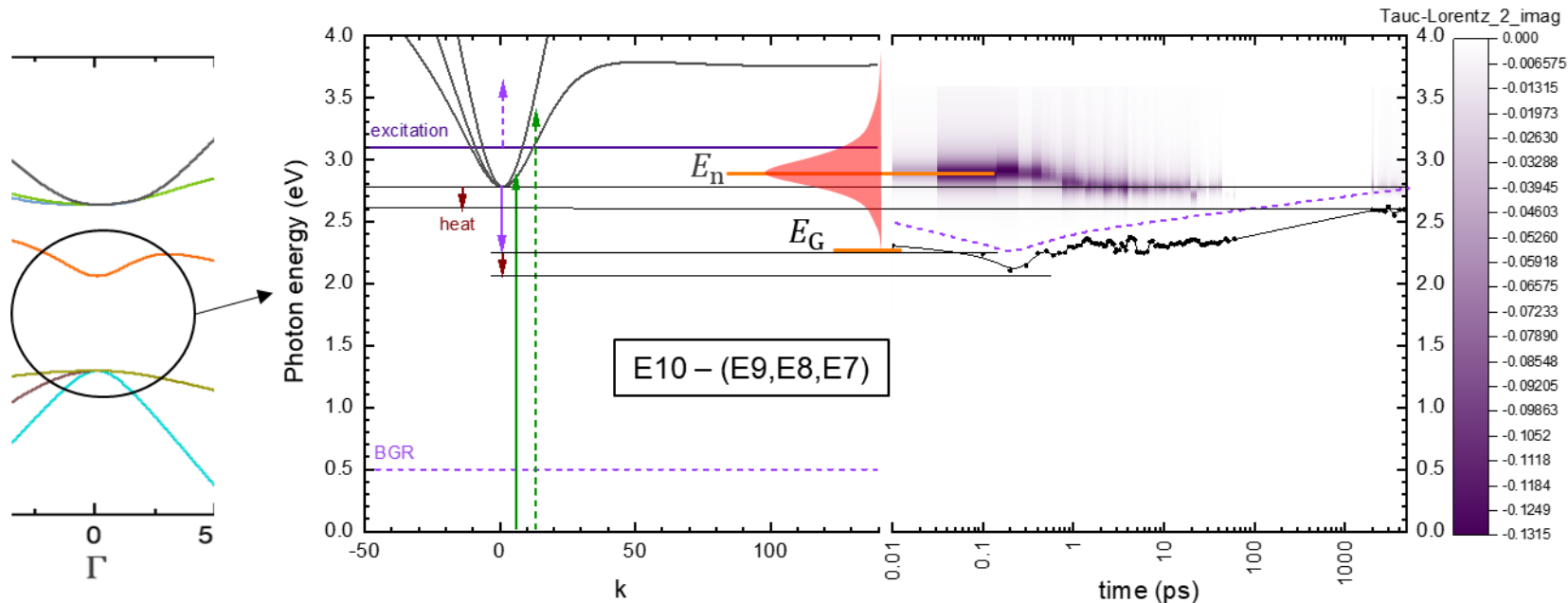


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- scattering into entire Brillouin zone within energy range $\Delta E_{\text{excitation}} + \Delta E_{\text{BGR}}$

example GaP: we obtain ΔE_{BGR} from time evolution of E_G of the TcL describing blocking at Γ
in the graph the energy difference of the lowest CB to the uppermost VBs is displayed

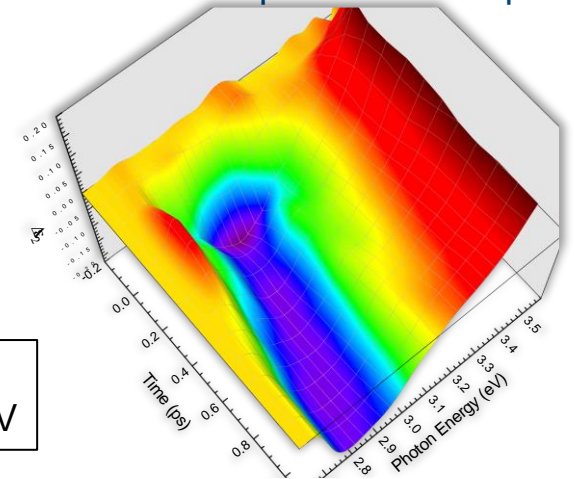
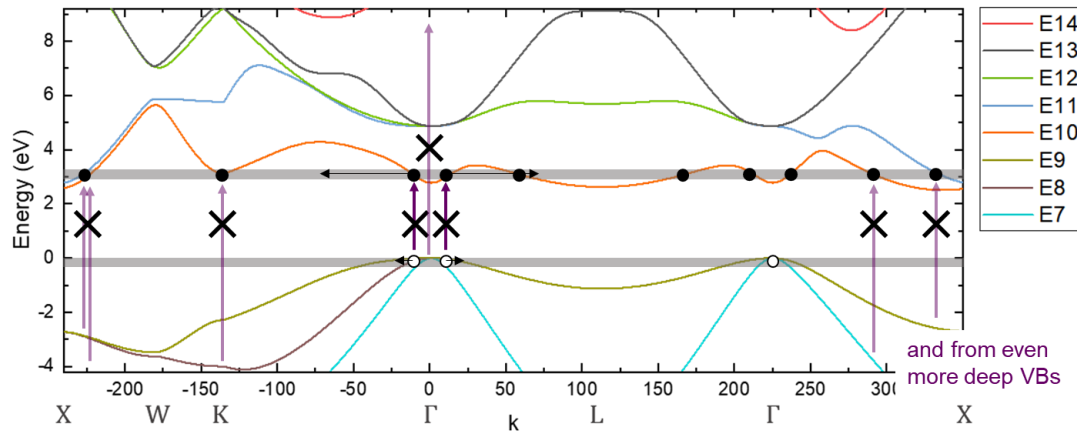


additional red-shift contribution for later time by heating due to energy transfer to the lattice

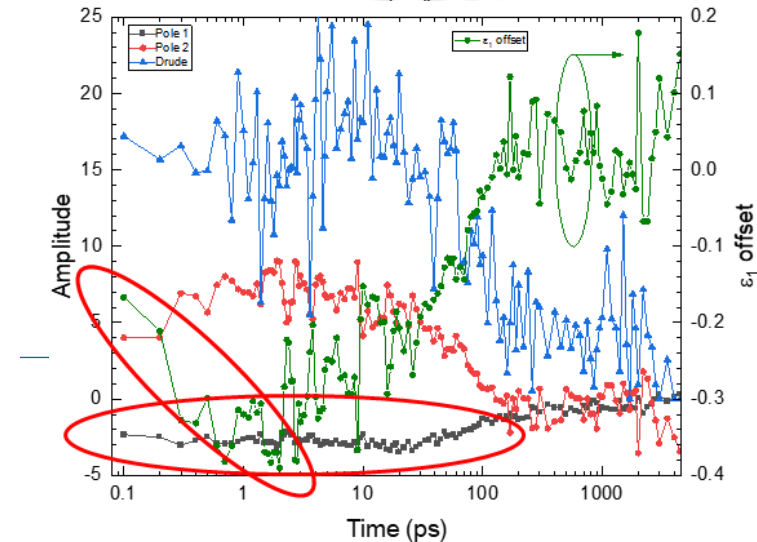
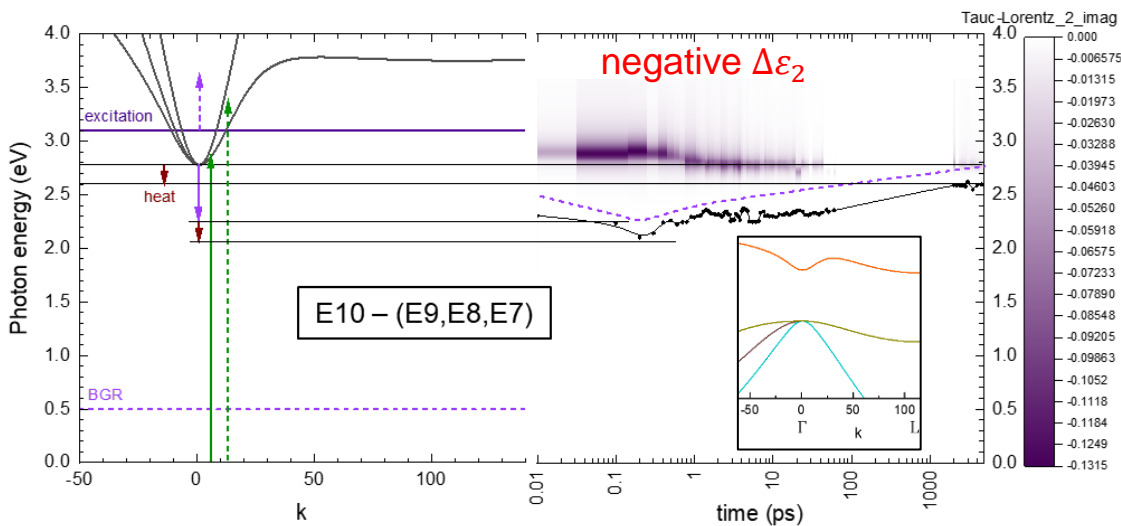
The tale of electrons – Excitation and shortly after

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GaP
3.1 eV

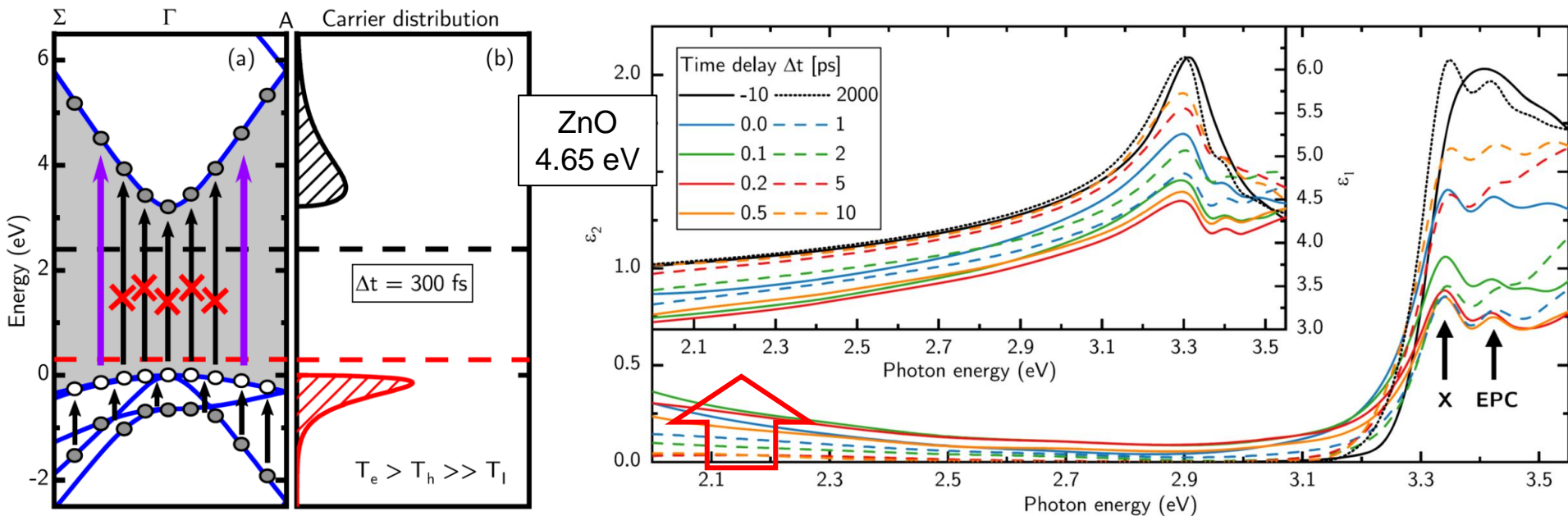


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1.: intra-VB transition near Γ (electrons: lower VB to topmost VB; holes: lowest to higher hole bands)

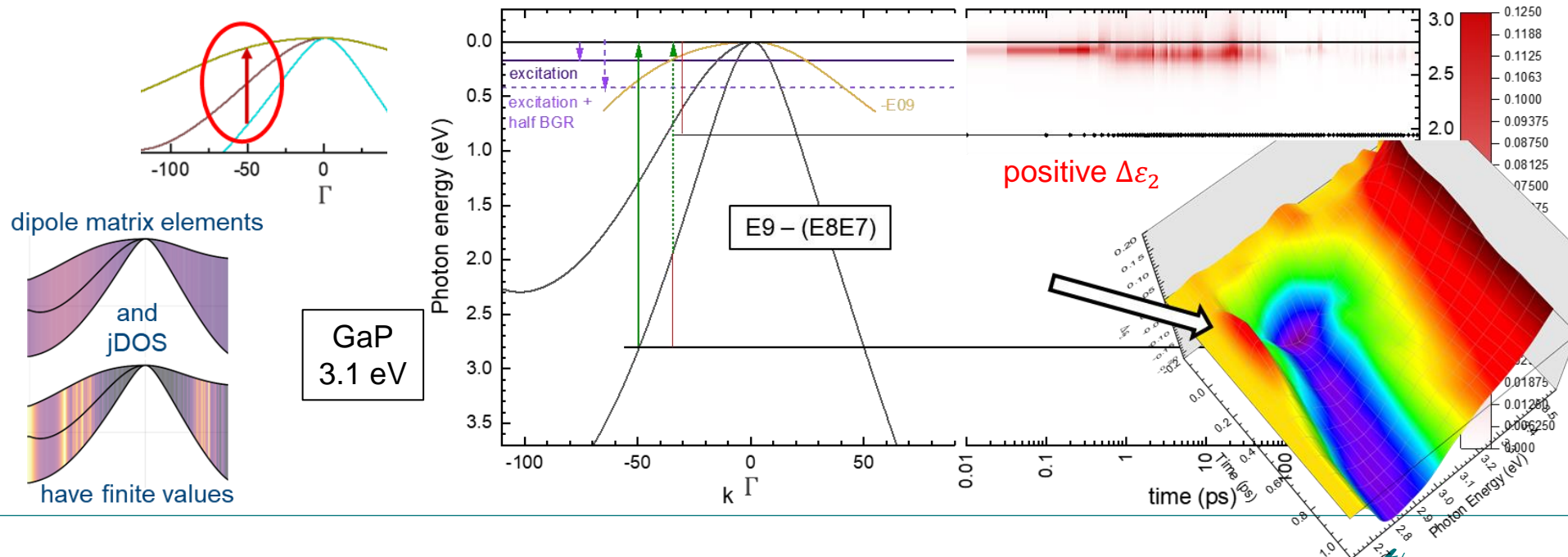


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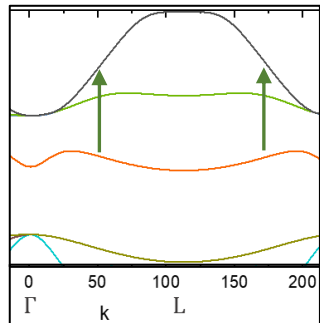


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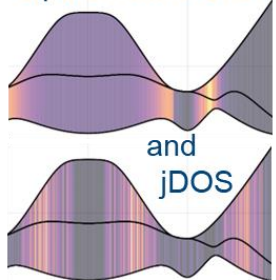
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2.: intra-CB transitions along L (hot electrons from lowest CB to higher conduction bands)



dipole matrix elements



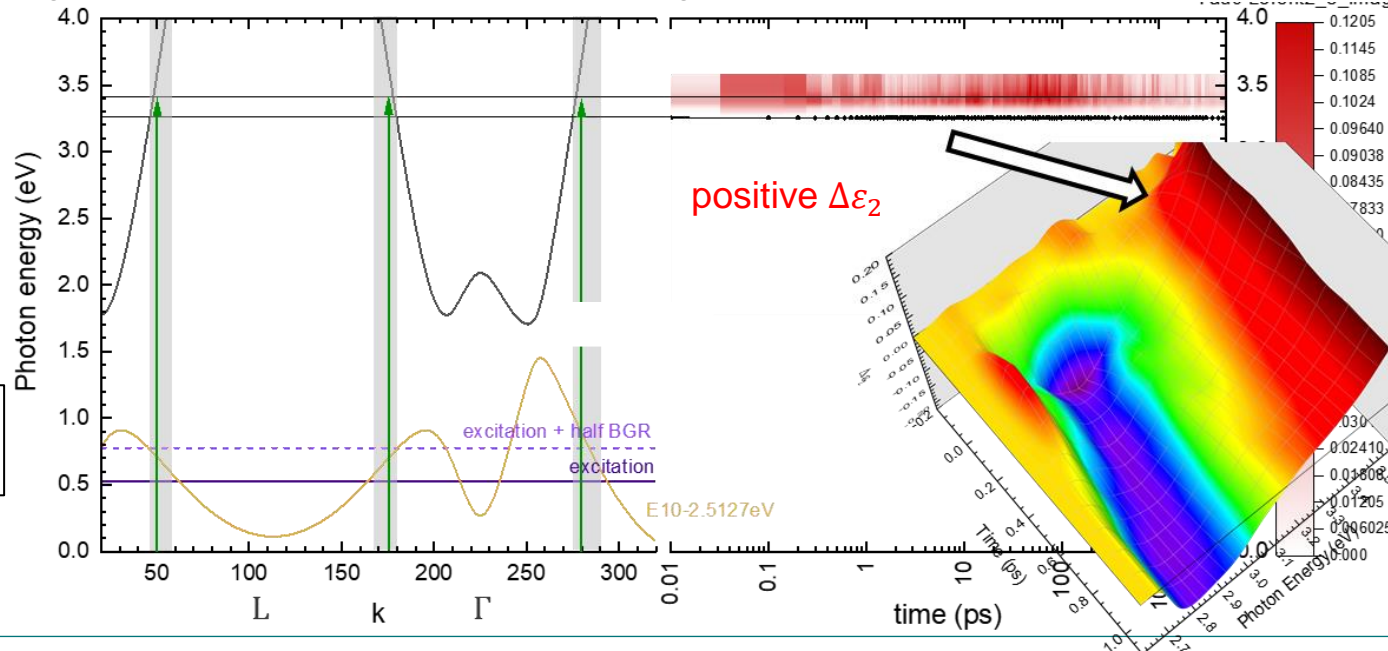
have finite values

but:

DPM quite weak

→ stationary theory correct?

GaP
3.1 eV



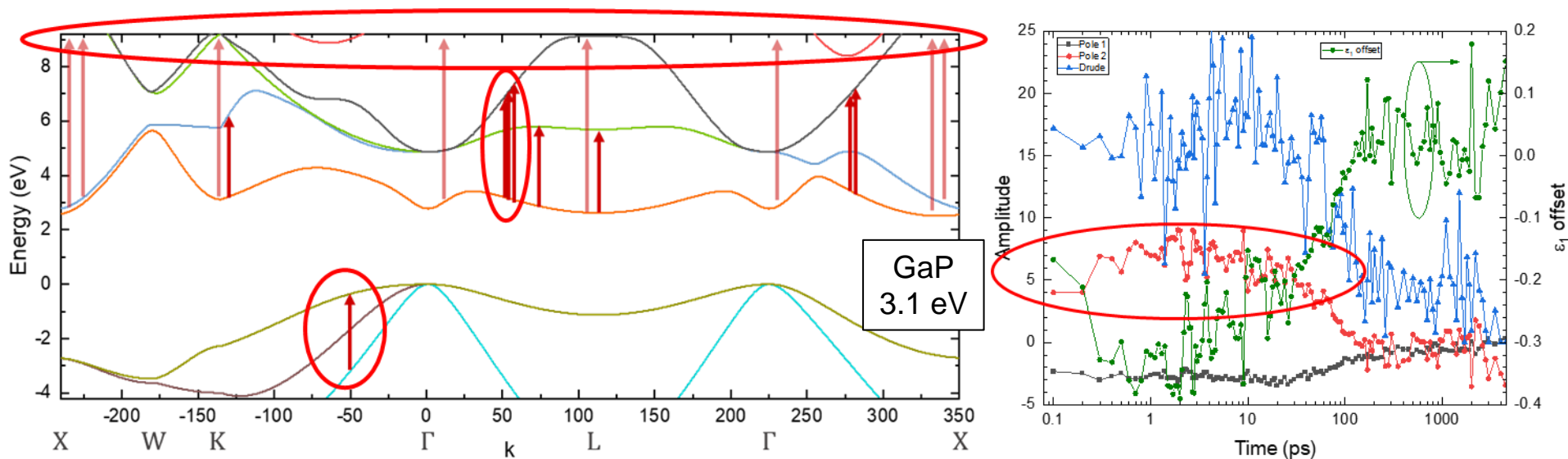
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2.: intra-CB transitions along L (hot electrons from lowest CB to higher conduction bands)

... and to higher bands (outside spectral range) expressed by positive pole



The tale of electrons – Excitation and shortly after

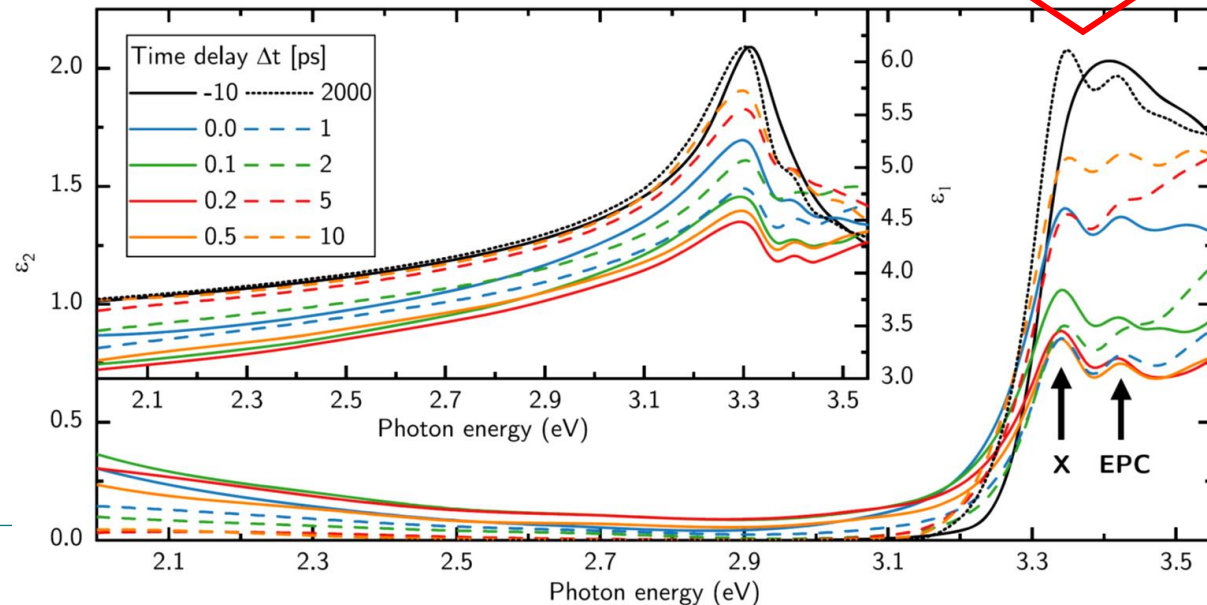
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ZnO
4.65 eV

excitons persisted at any time although exceeding Mott density → not only screening length matters, but also wavevector – at high excess-energy, strong non-parabolicity → misfit → reduced screening → Mahan excitons

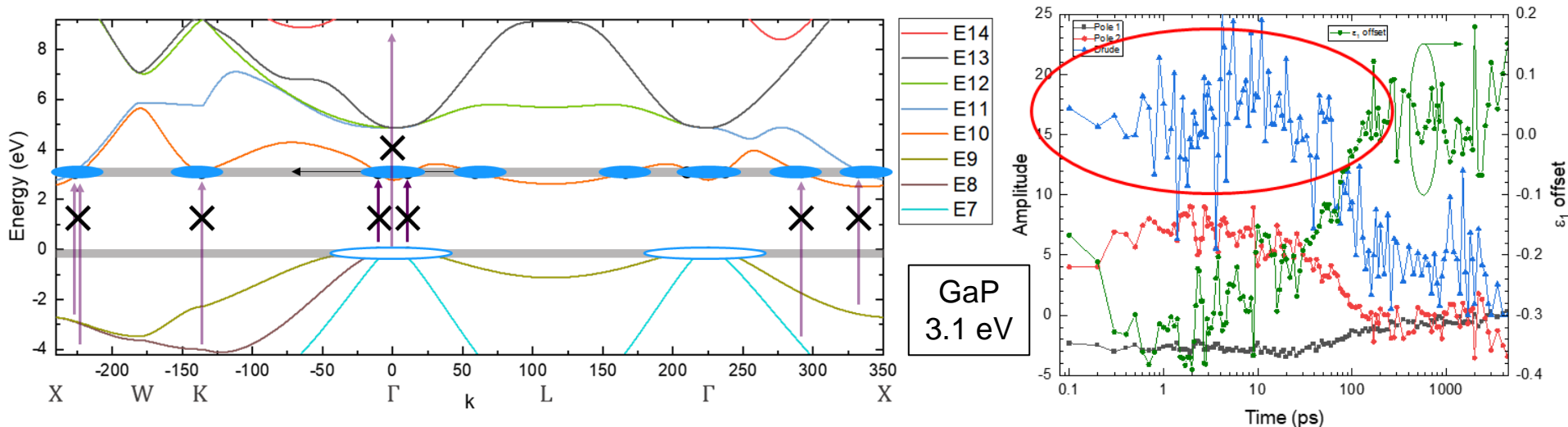
Schleife et al, Phys. Rev. Lett. 107 236405



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- collective free charge carrier oscillations (Drude) – electron and hole lakes in CB and VB



The tale of electrons – in the following ps

in the following time (sub-ps ... ps), excited carriers scatter amongst each other and with the lattice (phonons):

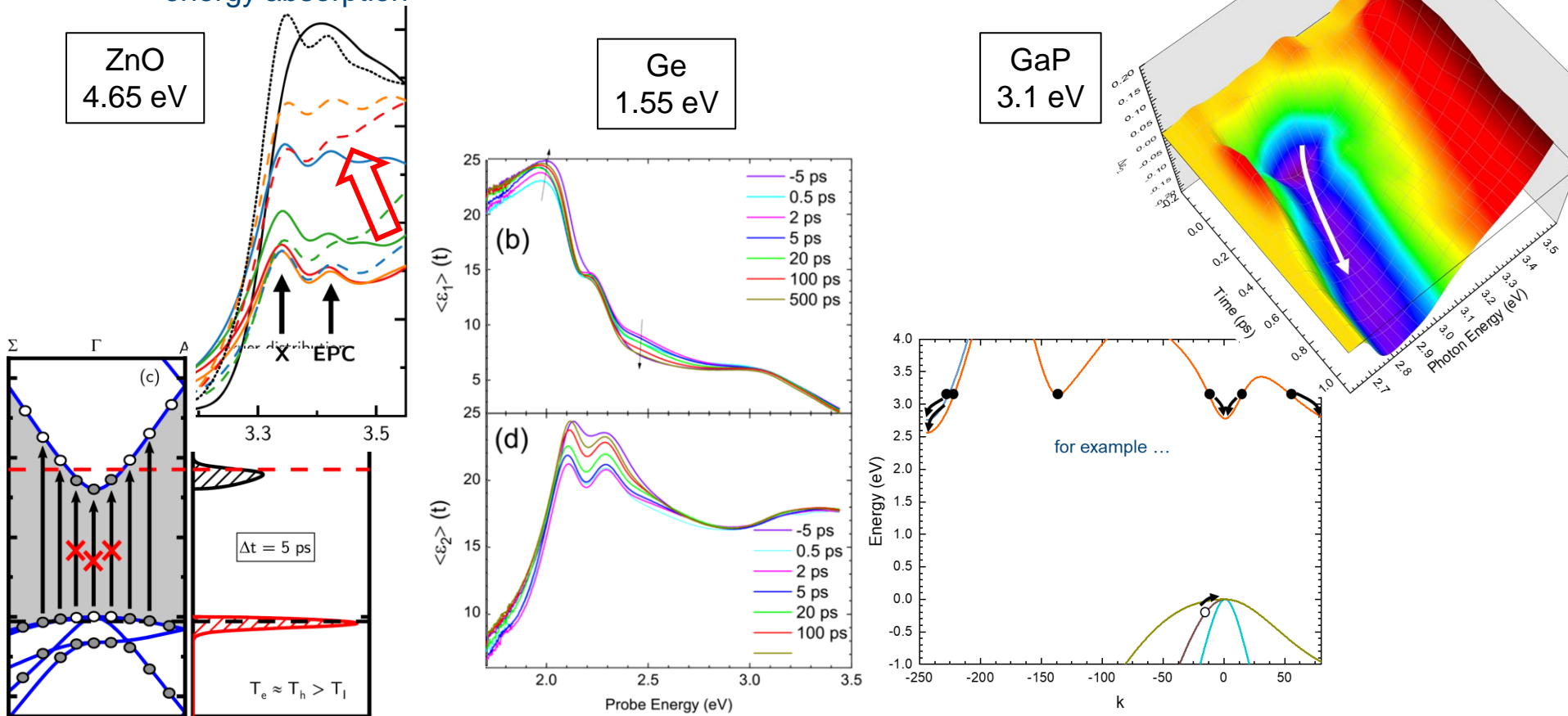
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finally, the system relaxes back to equilibrium either due to radiative or non-radiative carrier recombination within, depending on the material, some tens of ps (e.g. ZnO) or up to several ns (e.g. GaP)

The tale of electrons – in the following ps

in the following time (sub-ps ... ps), excited carriers scatter amongst each other and with the lattice (phonons):

- energy dissipation as heat → redshift of transition energies
- relaxation to band minima → redshift of the Pauli blocked absorption features and recovery of high-energy absorption



The tale of electrons – in the following ps

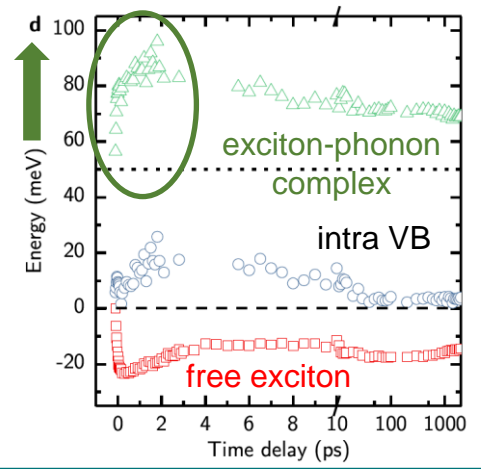
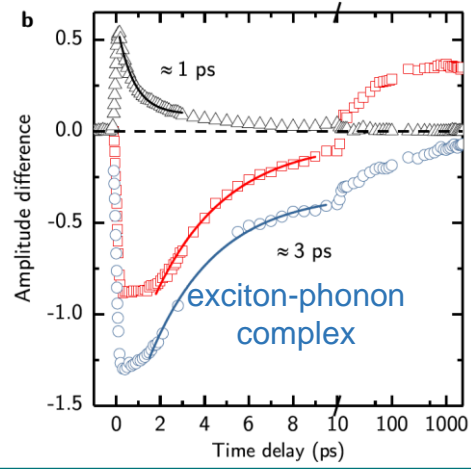
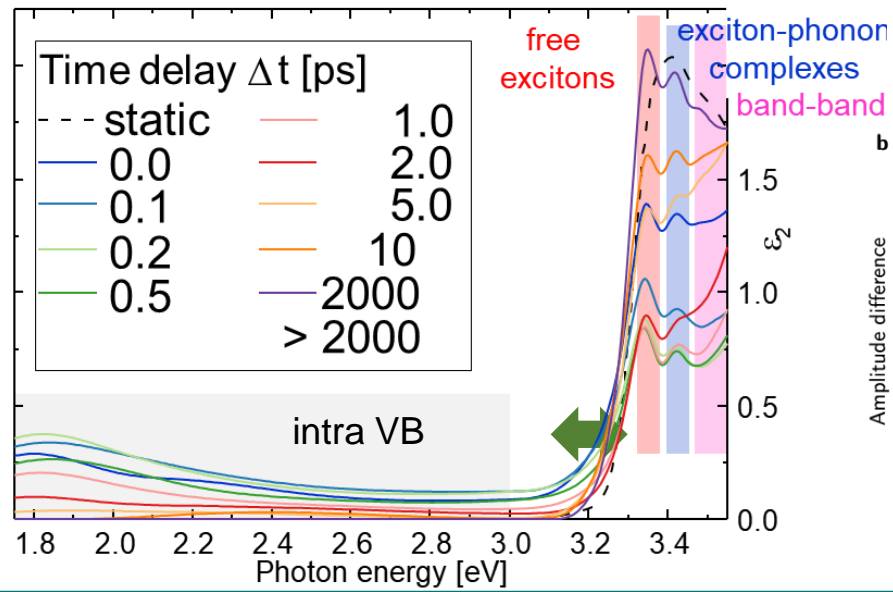
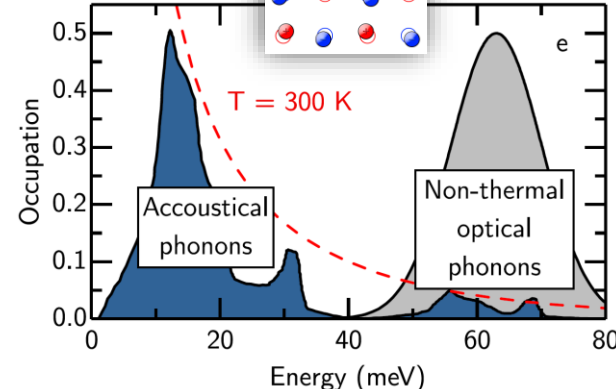
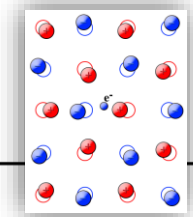
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electron thermalization slowed down by hot-phonon effect:

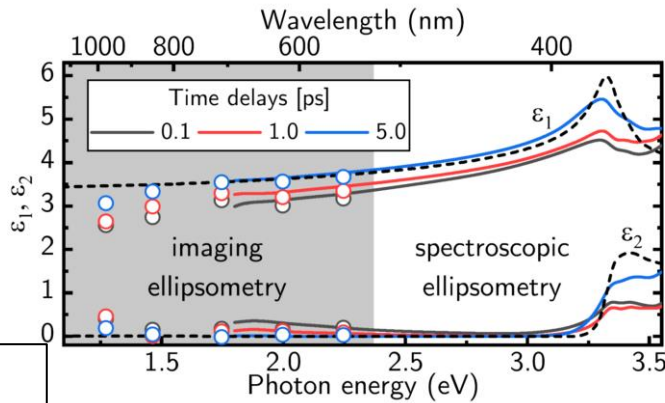
- electron-phonon scattering: creation of hot phonons
- in turn hot electrons created by phonon decay
- exciton-phonon binding energy increases
- high-energy exciton-phonon complex (exciton-polaron)

ZnO
4.65 eV

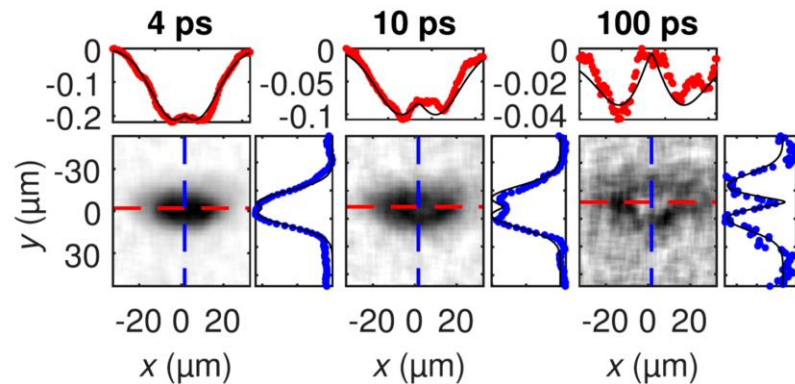
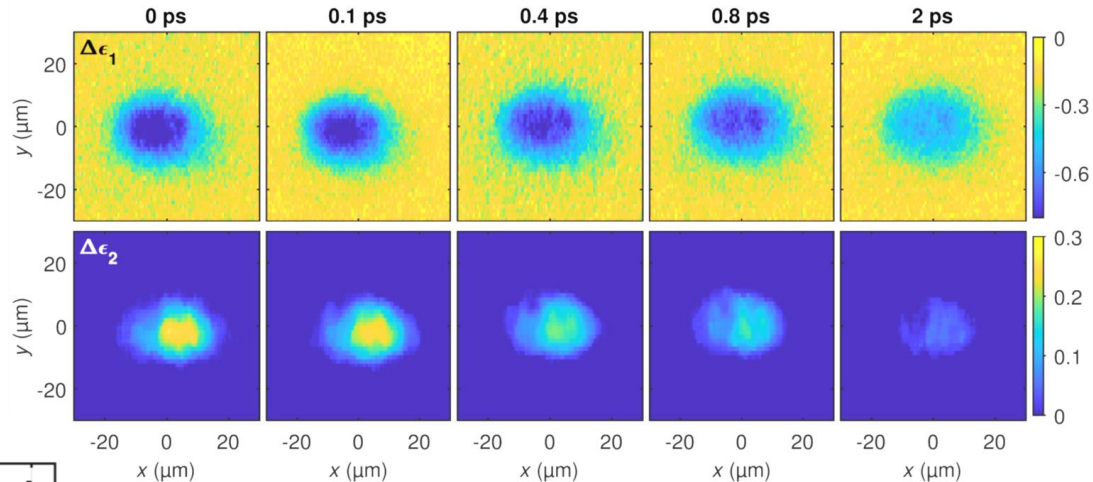
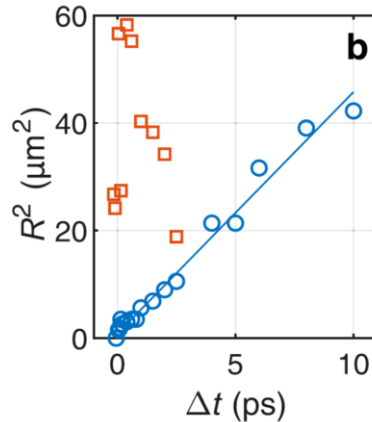
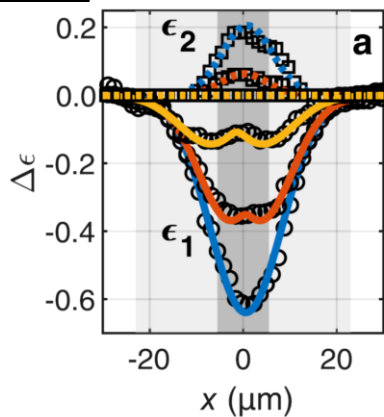


The tale of electrons – in the following ps

→ hot electrons can propagate ballistically over several μm



ZnO
4.67 eV



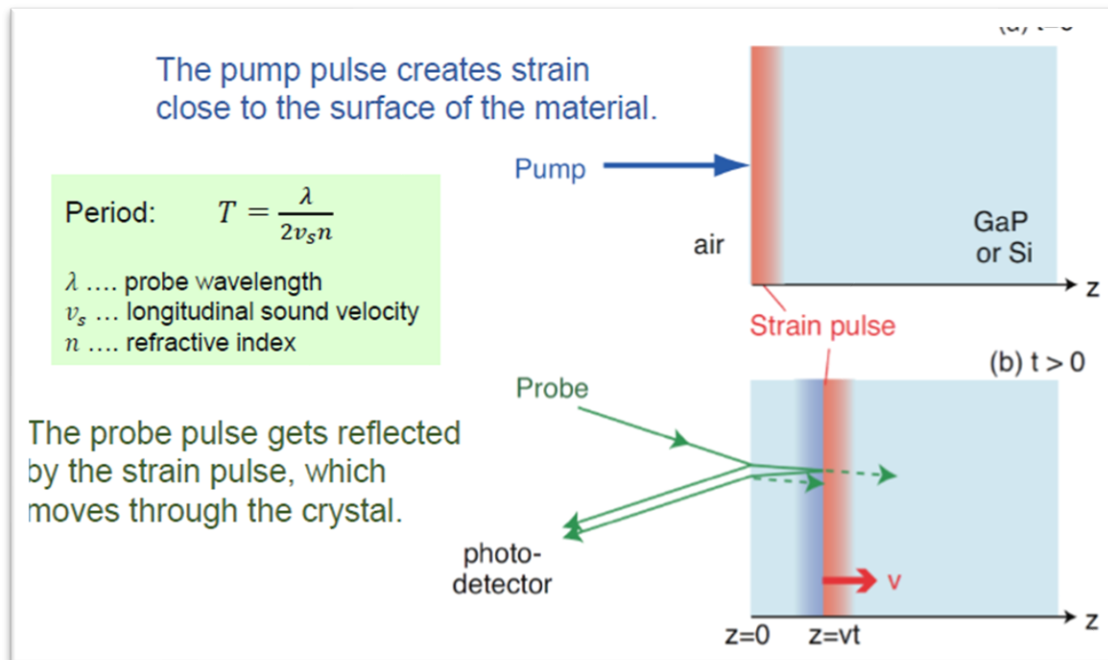
→ combined effect of carrier cooling and fast carrier transport: effective diffusion coefficient $1.1 \times 10^4 \text{ cm}^2/\text{s}$

→ ring structure: can be explained by a random-walk model including ballistic transport due to the thermal gradient induced by the hot-phonon effect (speed several 10^5 m/s , electron by 2.5 times faster than holes)

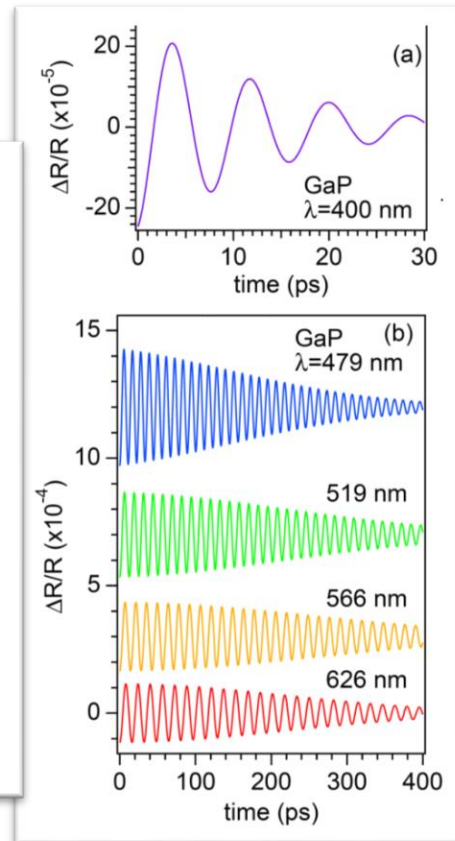
The tale of electrons – in the following ps

in the following time (sub-ps ... ps), excited carriers scatter amongst each other and with the lattice (phonons):

- energy dissipation as heat → redshift of transition energies
- relaxation to band minima → redshift of the Pauli blocked absorption features
- formation of hot-electron–hot-phonon states (hot exciton-phonon complexes)
- hot electrons can propagate ballistically over several μm
- phonons oscillate coherently

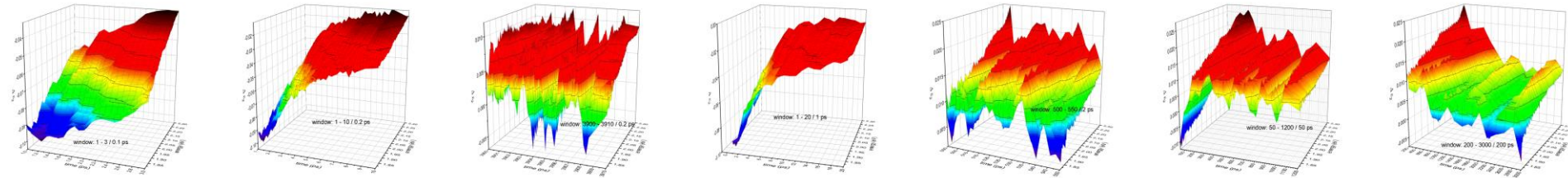


K. Ishioka, V. Rustagi, U. Höfer, H. Petek, and C. J. Stanton, Phys. Rev. B 95, 035205 (2017).

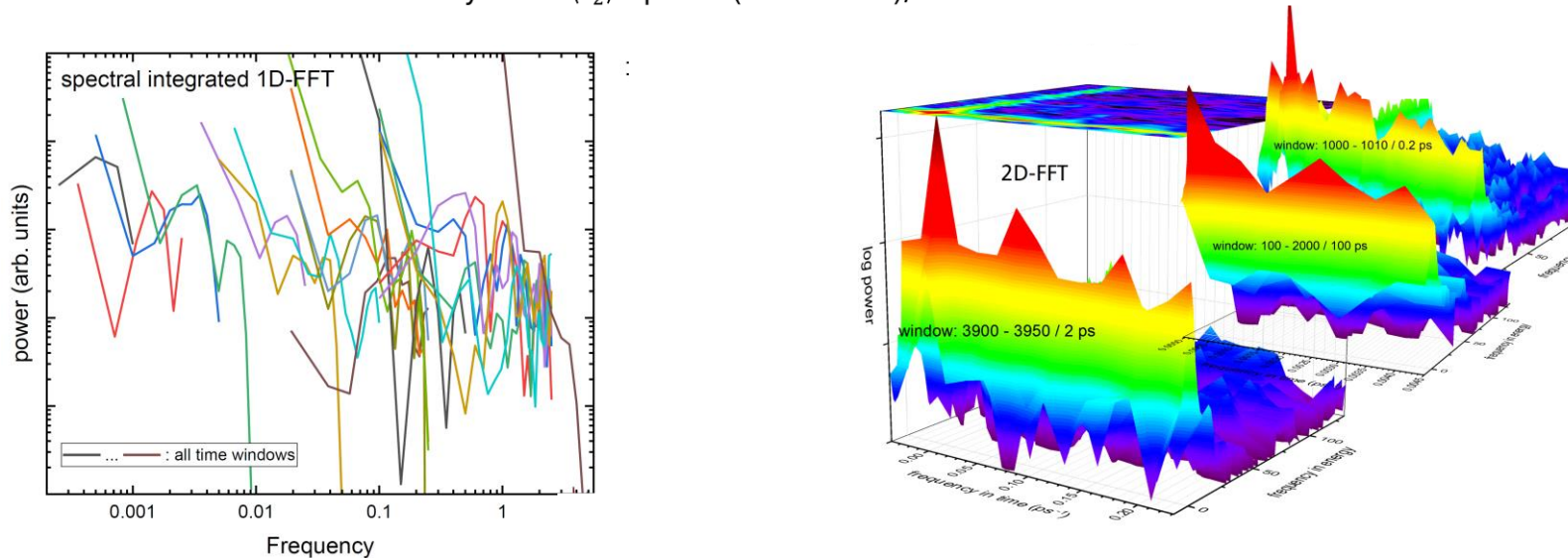


Long-lasting coherent phonon oscillations in Gallium Phosphide

time-delayed spectra recorded in various windows with different time steps from 0.1 to 500ps distributed in the full time range up to 4500ps examples for $\Delta\langle\varepsilon_2\rangle$ -spectra for some windows:



Fourier-analysis of $\Delta\langle\varepsilon_2\rangle$ -spectra (1.8 – 2.3 eV), two methods:



Long-lasting coherent phonon oscillations in Gallium Phosphide

⇒ yields a large bunch of frequencies:

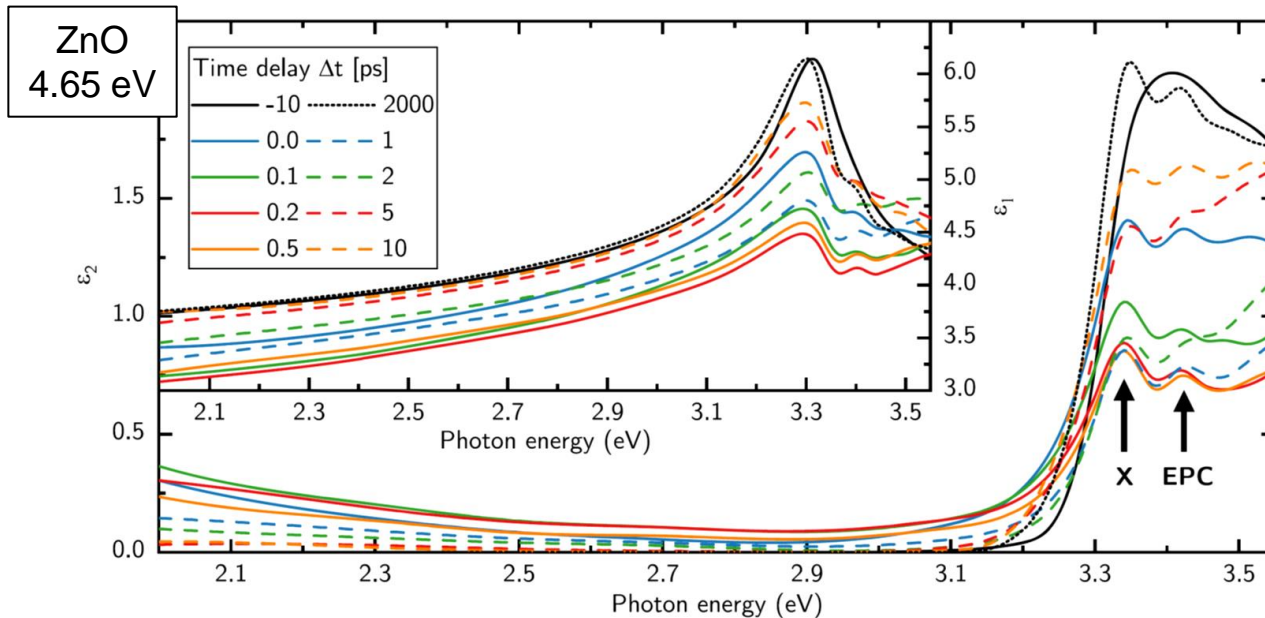
- allow only those who have at least 3 data points (step width) per period and 3 periods per window
- averaging of frequencies bunching together
- interferences of probe-light within a cavity, where one mirror is formed by the propagating sound wave (density wave) – varying cavity length in time
- related sound velocity according: $T = \frac{1}{\nu} = \frac{\lambda}{2nv_s}$

The tale of electrons – long-time story

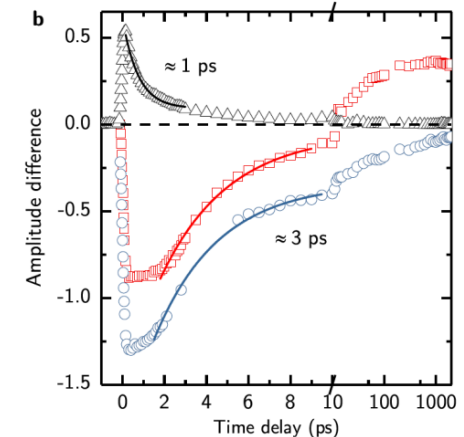
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- hot electrons can propagate ballistically over several μm
- phonons oscillate coherently

finally, the system relaxes back to equilibrium either due to radiative or non-radiative carrier recombination within, depending on the material, some tens of ps (e.g. ZnO) or up to several ns (e.g. GaP)



fast radiative recombination
(emission dynamics:
photoluminescence / lasing)

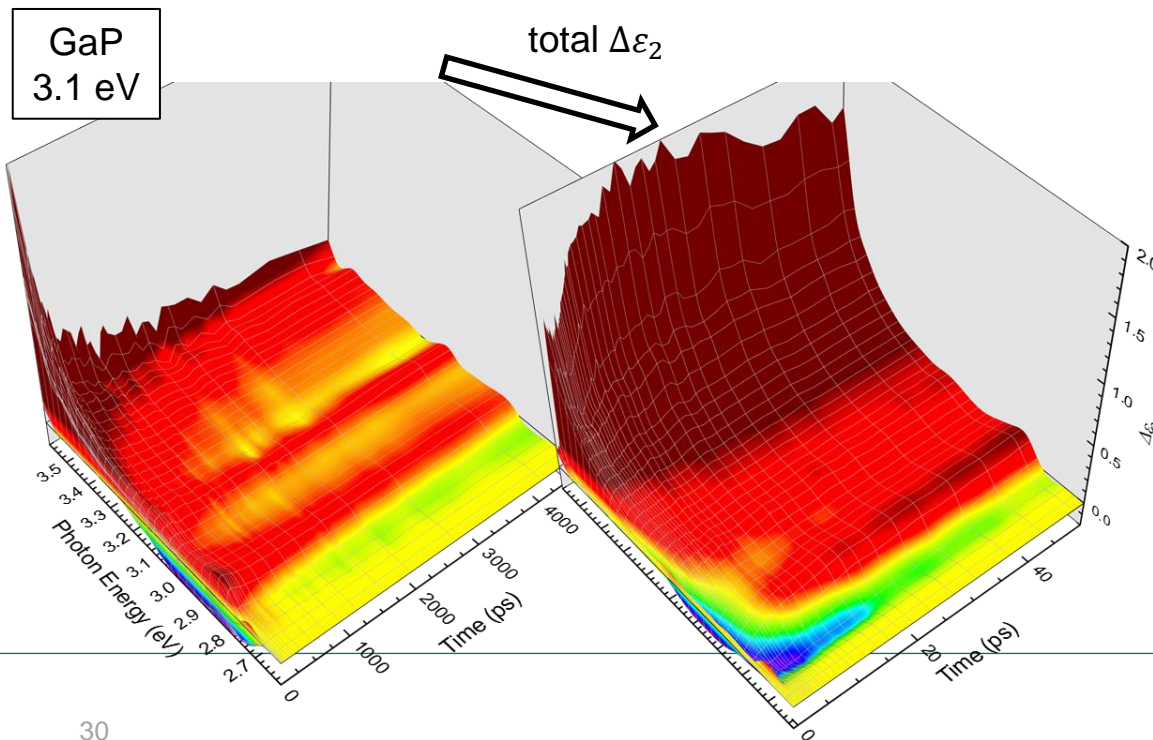


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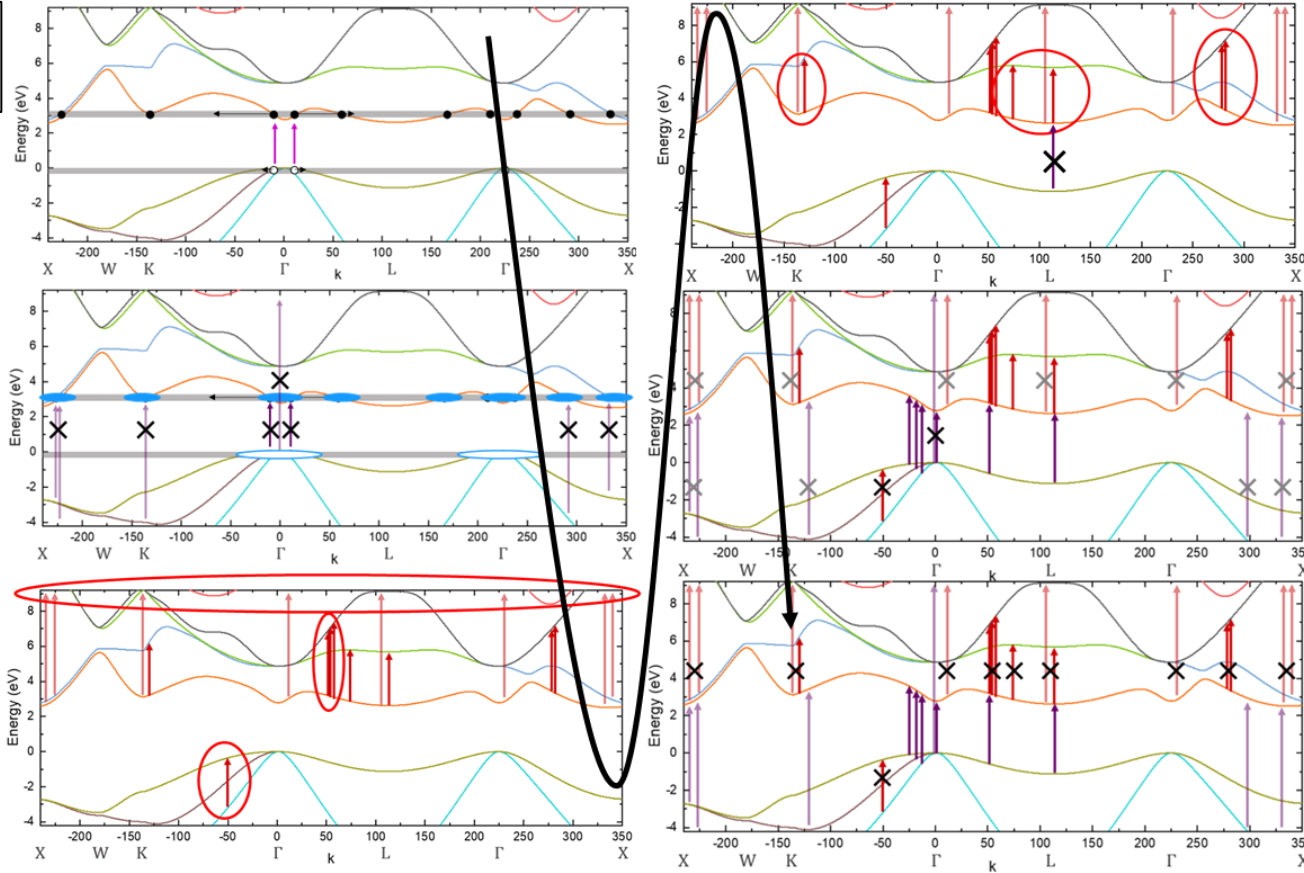
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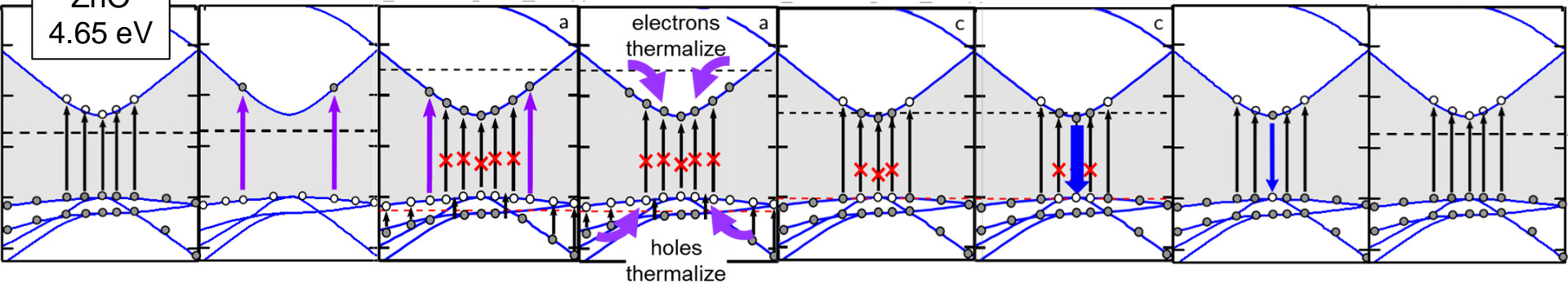
- additional total oscillator strength due to intra-CB transitions peaks at around 20...40 ps
- no complete recovery after 4 ns (next pump only after 1 ms)

The tale of electrons

GaP
3.1 eV



ZnO
4.65 eV



The tale of electrons

exciting with high-intense laser beam: electrons and holes occupy formerly “empty” conduction (CB) and valence (VB) band states → hot charge carriers with temperatures up to several thousands of Kelvin

- carriers spread within the entire Brillouin zone (BZ) to energetically matching bands
- band gap renormalization (BGR) → redshift of transition energies between VB and CB
- transitions between now occupied states are Pauli-blocked → reduction of absorption at the respective energies
- excess electrons and holes can be excited by the probe light → arising of new intra VB and/or intra CB transitions → increase of absorption at the respective energies
- when the material exhibits excitons: they are screened by the excited carriers, but may also form so-called Mahan excitons → energy redshift and absorption bleaching
- collective free charge carrier oscillations (Drude)

in the following time (sub-ps ... ps), excited carriers scatter amongst each other and with the lattice (phonons):

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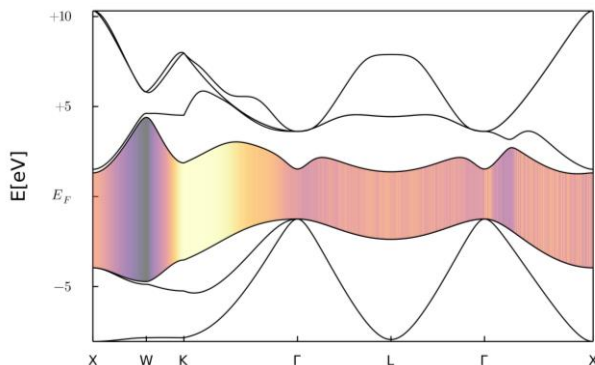
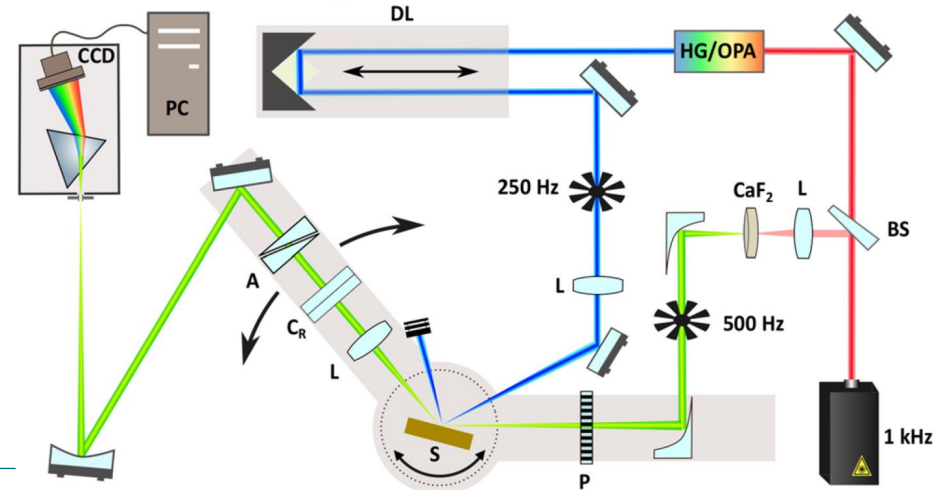
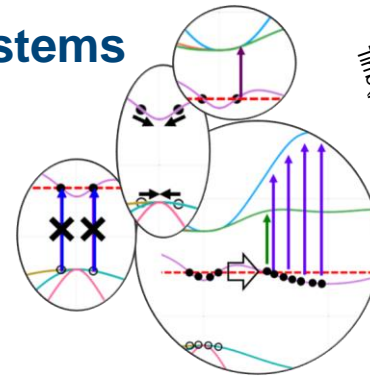
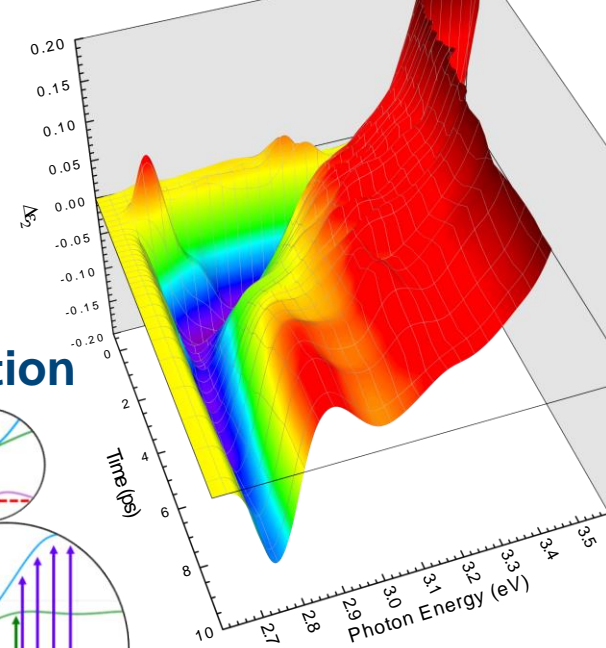
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Summary

Pump-probe fs-TSE

André, Carola, Marcus, Mateusz, Noah, Oliver, Shirly, Stefan, Steffen, Theo, Younes

- method recently developed by us
- time evolution of the full complex dielectric function
- already applied to several material systems
 - intra-band transitions (VB-VB and CB-CB)
 - hot-phonon scattering
 - ballistic carrier propagation
 - transient birefringence changes
 - coherent acoustic phonon oscillations
 - spectral weight transfer



Summary

Review of
Scientific Instruments

ARTICLE







Steffen Richter, Mateusz Rebarz, Oliver Herrfurth, Shirly Espinoza, Rüdiger Schmidt-Grund, and Jakob Andreasson *Rev. Sci. Instrum.* **92**, 033104 (2021)

Broadband femtosecond spectroscopic ellipsometry

Femtosecond-time-resolved imaging of the dielectric function of ZnO in the visible to near-IR spectral range












Cite as: *Appl. Phys. Lett.* **115**, 212103 (2019); <https://doi.org/10.1063/1.5128069>

Submitted: 16 September 2019 . Accepted: 05 November 2019 . Published Online: 19 November 2019

O. Herrfurth , T. Pflug , M. Olbrich , M. Grundmann , A. Horn , and R. Schmidt-Grund 

PHYSICAL REVIEW RESEARCH **3**, 013246 (2021)

Transient birefringence and dichroism in ZnO studied with fs-time-resolved spectroscopic ellipsometry

O. Herrfurth ,^{1,*} S. Richter ,^{2,3} M. Rebarz ,³ S. Espinoza ,³ J. Zúñiga-Pérez ,⁴ C. Deparis ,⁴ J. Leveillee ,⁵ A. Schleife ,
M. Grundmann ,¹ J. Andreasson ,³ and R. Schmidt-Grund 

New Journal of Physics












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IOP Institute of Physics

PAPER

New J. Phys. **22** (2020) 083066

Ultrafast dynamics of hot charge carriers in an oxide semiconductor probed by femtosecond spectroscopic ellipsometry

Steffen Richter^{1,2,7,8} , Oliver Herrfurth^{3,8} , Shirly Espinoza¹ , Mateusz Rebarz¹ ,
Miroslav Kloz¹ , Joshua A Leveillee¹ , André Schleife¹ , Stefan Zollner^{4,5} ,
Marius Grundmann¹ , Jakob Andreasson¹  and Rüdiger Schmidt-Grund^{2,8} 

RESEARCH ARTICLE *Phys. Status Solidi RRL* **2022**, *16*, 2200058

15 years of pss RRL



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Coherent Acoustic Phonon Oscillations and Transient Critical Point Parameters of Ge from Femtosecond Pump-Probe Ellipsometry

Carola Emminger,* Shirly Espinoza, Steffen Richter, Mateusz Rebarz, Oliver Herrfurth, Martin Zahradník, Rüdiger Schmidt-Grund, Jakob Andreasson, and Stefan Zollner

Transient dielectric functions of Ge, Si, and InP from femtosecond pump-probe ellipsometry

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Submitted: 14 May 2019 . Accepted: 01 July 2019 . Published Online: 01 August 2019

Shirly Espinoza, Steffen Richter, Mateusz Rebarz, Oliver Herrfurth, Rüdiger Schmidt-Grund , Jakob Andreasson, and Stefan Zollner 

Thank You for Attention!

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J. Andreasson, C. Emminger, S. Espinoza, D. Franta, O. Herrfurth, K. Hingerl, A. Horn, M. Kloz, J. Leveillee, M. Olbrich, T. Pflug, M. Rebarz, S. Richter, E. Runge, A. Schleife, Y. Slimi, N. Stiehm, C. Sturm, S. Zollner, M. Zahradník



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